



# 2SA473

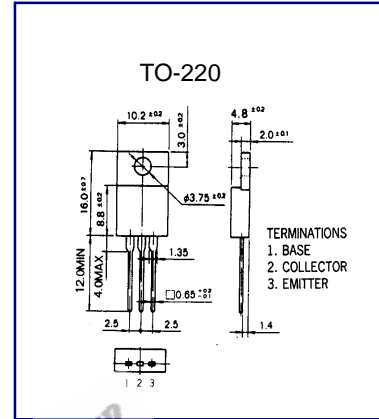
# PNP EPITAXIAL SILICON TRANSISTOR

## LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SC1173

### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-30	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-30	V
Emitter-Base voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-3	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	10	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> = 0			-10	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0			10	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -1V, I <sub>C</sub> = -0.1A	70		240	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -2A, I <sub>B</sub> = -0.2A			-0.8	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -2V, I <sub>C</sub> = -0.5A		100		MHZ